

# EPIGAP Optronik GmbH

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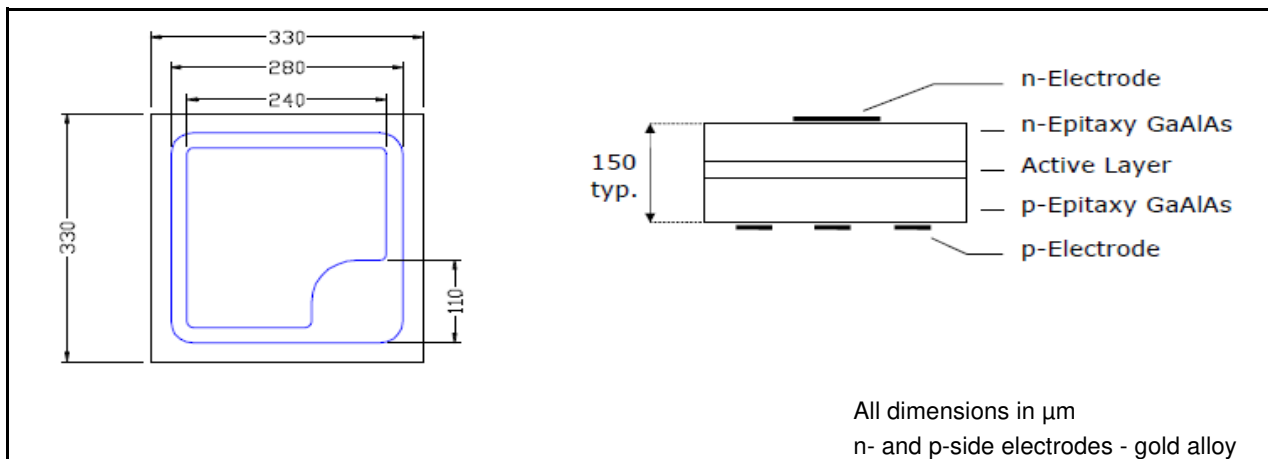
## Data Sheet

### LED Chip Infrared

### EOLC-810-25

Rev. 02, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs / AlGaAs, DHS	N (cathode) up



### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.5	1.8	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Radiant power*	$I_F = 20 \text{ mA}$	$\Phi_e$	3.5	4.5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	800	810	820	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		33		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		35; 30		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire bond side up

Art. No. 131 052



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.